Electronic Supplementary Material (ESI) for RSC Advances.

Band Gap Engineering of MnO_2through *In-situ* Al-doping for Applicable Pseudocapacitors

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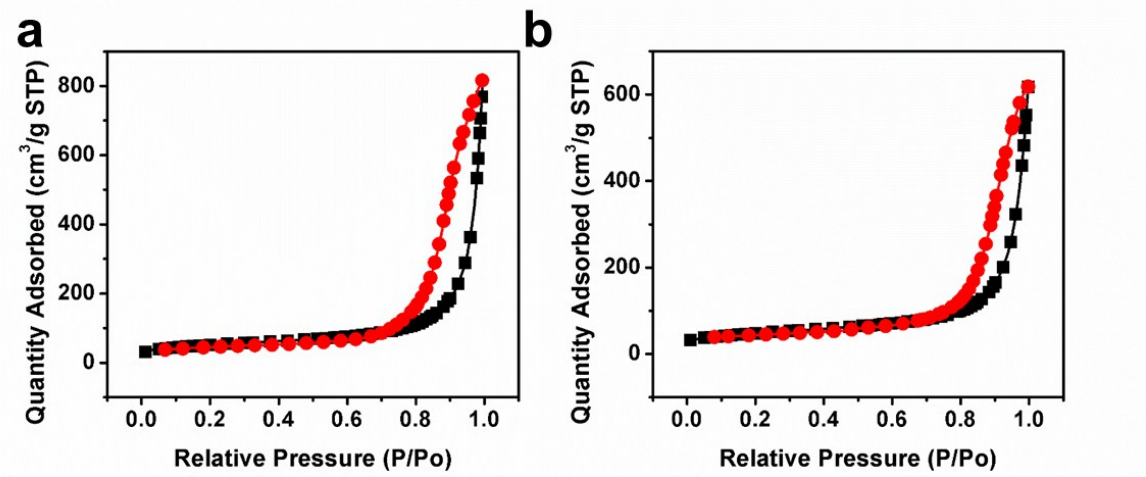

Fig. S1. N2 adsorption-desorption isotherms of ASM and ADM.

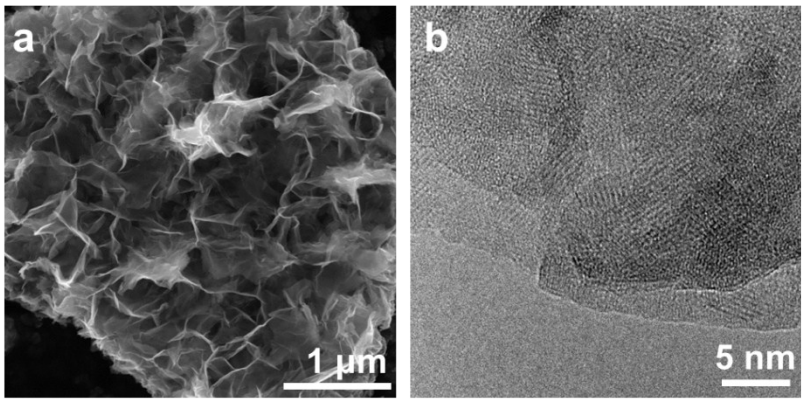

Fig. S2. SEM and TEM image of ASM, which shows same morphology of ADM.

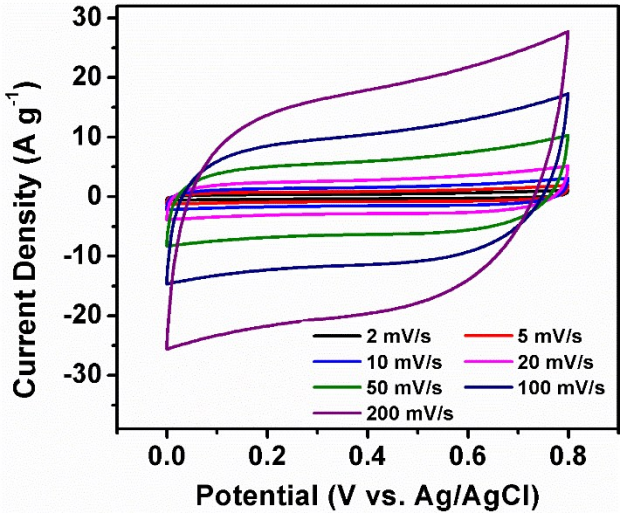

Fig. S3.CV curves of ASM from 2 mV s^{-1} to 200 mV s^{-1}.

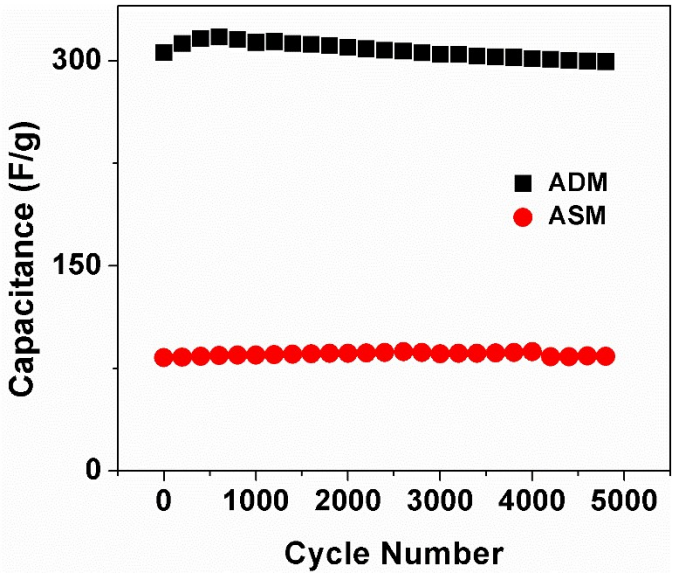

Fig. S4. The cycle testing of ADM and ASM through galvanostatic charge/dischargeat 2 Ag^{-1}.

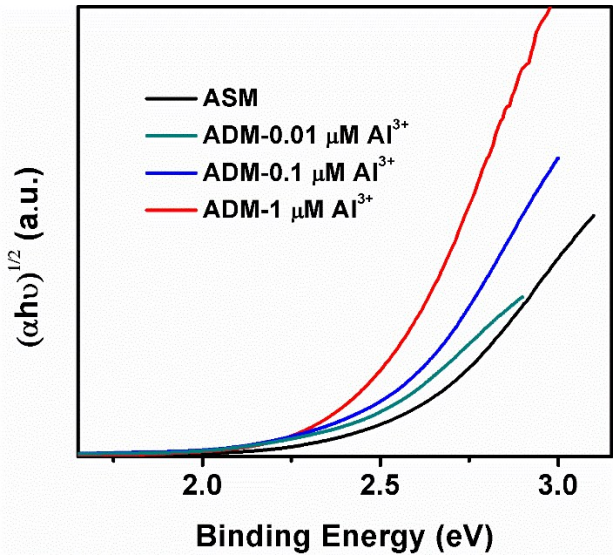

Fig. S5. UV-visible $(ahv)^{1/2}$ vs Ep curves for samples with different Al^{3+} concentration.